

N-channel 650V, 48A, 0.068Ω Super-Junction Power MOSFET

Features

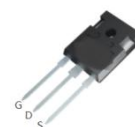
- ◆ Ultra-fast body diode
- ◆ Very low FOM $R_{DS(on)} \times Q_g$
- ◆ 100% UIS tested
- ◆ RoHS compliant

Applications

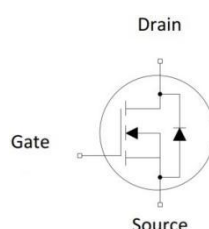
- ◆ Power factor correction (PFC).
- ◆ Switched mode power supplies (SMPS).
- ◆ Uninterrupted power supply (UPS).

Product Summary

$V_{DS} @ T_{j,25^\circ C}$	650V
$R_{DS(on),max}$	0.068Ω
I_D	48A
$Q_{g,typ}$	70 nC



TO-247



N-Channel MOSFET

Marking information

Product	Package	Marking	Packing method
SPW47N60CS	TO-247	SPW47N60	Tube

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	650	V
Continuous drain current ($T_C = 25^\circ C$)	I_D	48	A
($T_C = 100^\circ C$)		30.3	A
Pulsed drain current ¹⁾	I_{DM}	144	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ²⁾	E_{AS}	375	mJ
Avalanche current, repetitive ³⁾	I_{AR}	5	A
Power Dissipation TO-247 ($T_C = 25^\circ C$)	P_D	284	W
- Derate above $25^\circ C$		2.27	W/ $^\circ C$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$
Continuous diode forward current	I_S	48	A
Diode pulse current	$I_{S,pulse}$	144	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
		TO-247	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.44	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	39	$^{\circ}\text{C/W}$
Soldering temperature, wave soldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	$^{\circ}\text{C}$

Electrical Characteristics $T_c = 25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =1mA	650	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =1mA	3		5	V
Drain cut-off current	I _{DSS}	V _{DS} =650 V, V _{GS} =0 V, T _J = 25°C T _J = 125°C	- -	- 50	10	μA
Gate leakage current, Forward	I _{GSSF}	V _{GS} =30 V, V _{DS} =0 V	-	-	100	nA
Gate leakage current, Reverse	I _{GSSR}	V _{GS} =-30 V, V _{DS} =0 V	-	-	-100	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =24 A T _J = 25°C	- - -	0.057	0.068	Ω
Dynamic characteristics						
Input capacitance	C _{iSS}	V _{DS} = 100 V, V _{GS} = 0 V, f = 100KHz	-	3400	-	pF
Output capacitance	C _{oss}		-	120	-	
Reverse transfer capacitance	C _{rss}		-	4.3	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 400V, I _D = 24A R _G = 2.5Ω, V _{GS} =10V	-	32	-	ns
Rise time	t _r		-	32	-	
Turn-off delay time	t _{d(off)}		-	42	-	
Fall time	t _f		-	22.5	-	
Gate charge characteristics						
Gate to source charge	Q _{gs}	V _{DD} =480 V, I _D =24A, V _{GS} =0 to 10 V	-	22	-	nC
Gate to drain charge	Q _{gd}		-	28	-	
Gate charge total	Q _g		-	70	-	
Gate plateau voltage	V _{plateau}		-	6.6	-	V
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =48A	-	-	1.2	V
Reverse recovery time	t _{rr}	V _R =300 V, I _F =24A, dI _F /dt=100 A/μs	-	200	-	ns
Reverse recovery charge	Q _{rr}		-	1.4	-	μC
Peak reverse recovery current	I _{rrm}		-	13.7	-	A

Notes:

- Limited by maximum junction temperature, maximum duty cycle is 0.75.
- $L = 30\text{mH}$, $V_{\text{DD}} = 50\text{V}$, Starting $T_j = 25^{\circ}\text{C}$.

Electrical Characteristics Diagrams

Figure 1. Output Characteristics

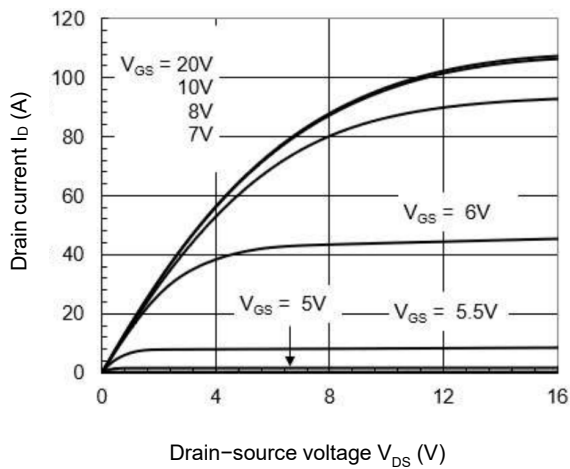


Figure 2. Transfer Characteristics

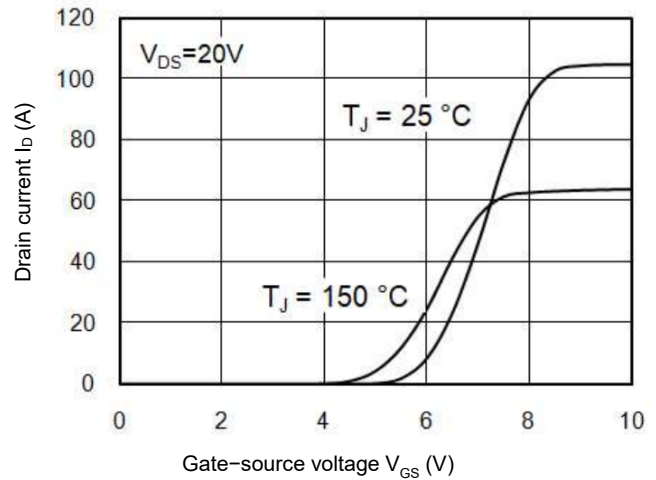


Figure 3. On-Resistance vs. Drain Current

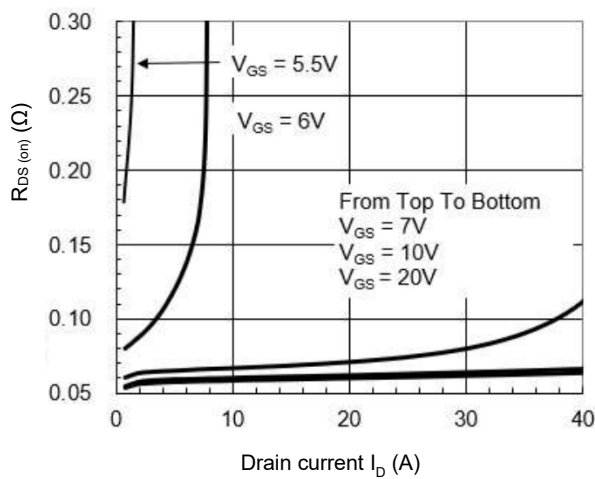


Figure 4. Capacitance Characteristics

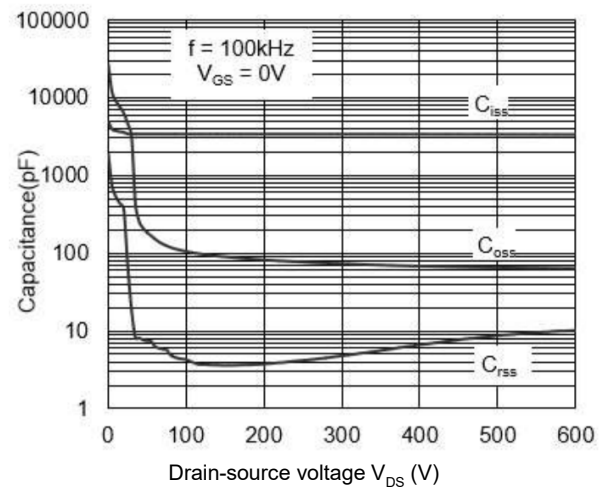


Figure 5. Gate Charge Characteristics

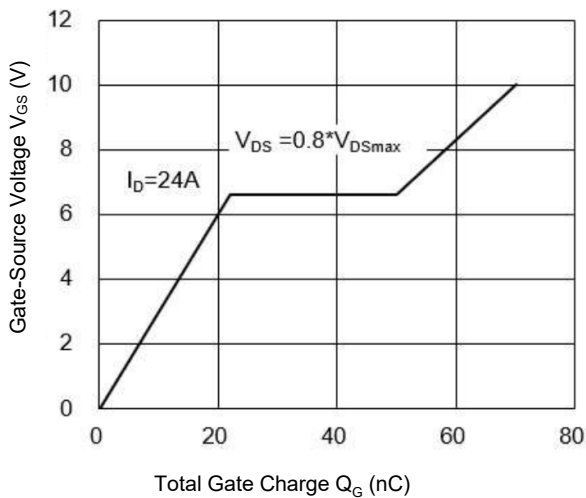


Figure 6. Body Diode Forward Voltage

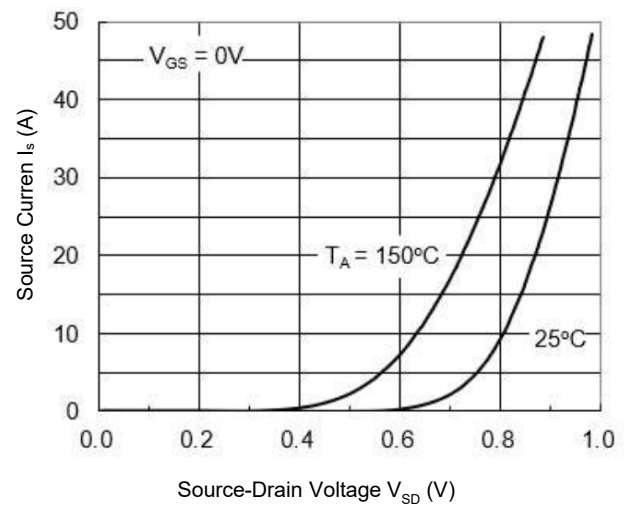


Figure 7. Breakdown Voltage vs. Temperature

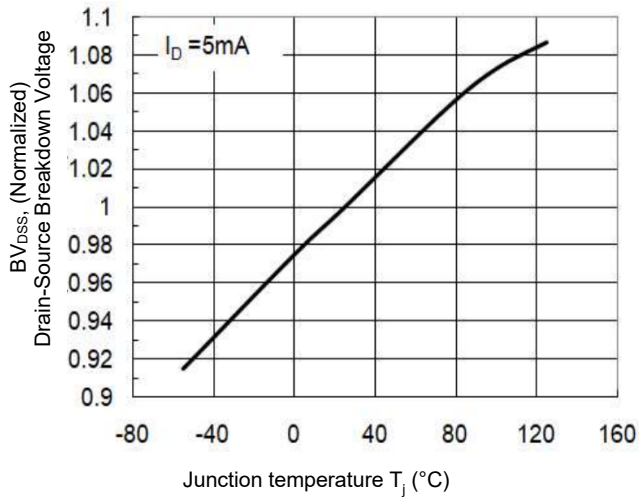


Figure 8. On-Resistance vs. Temperature

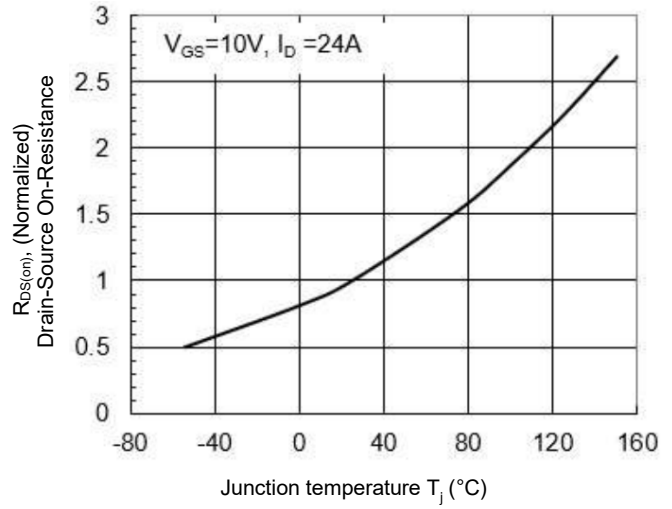
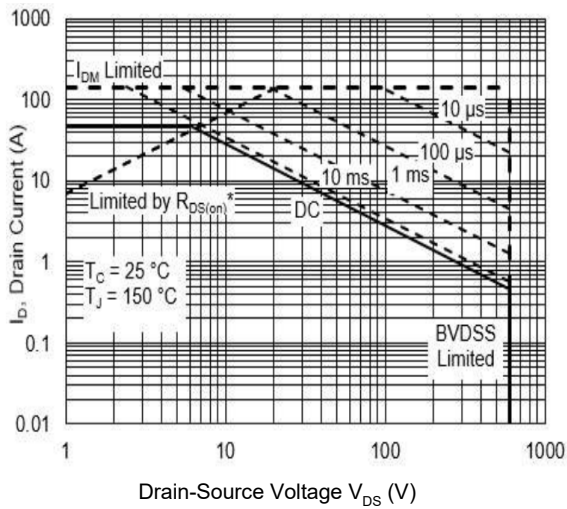
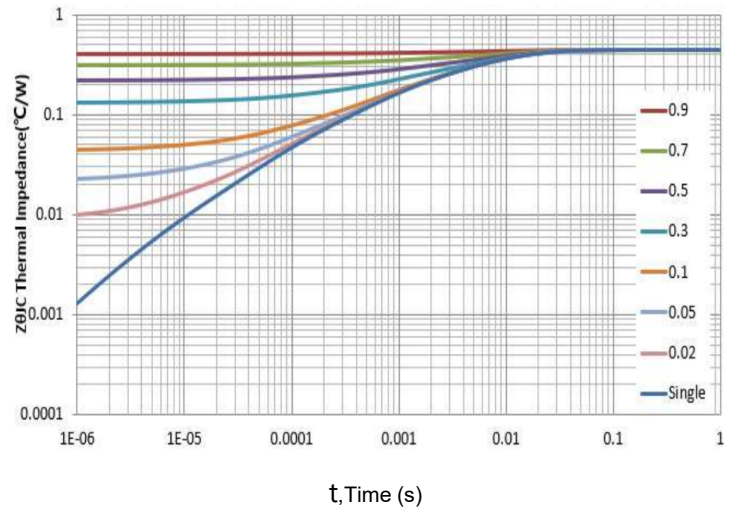
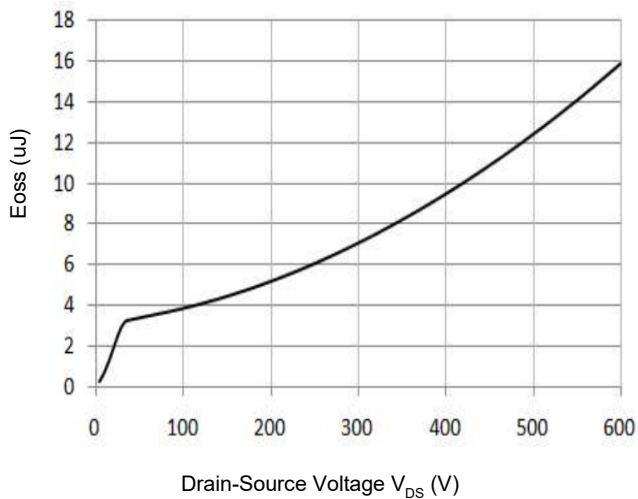
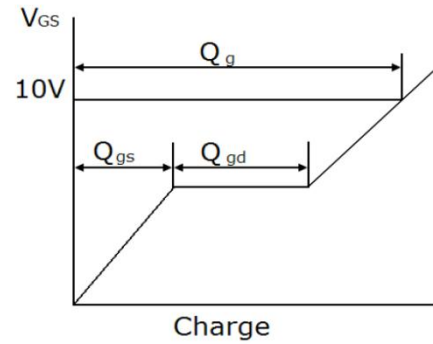
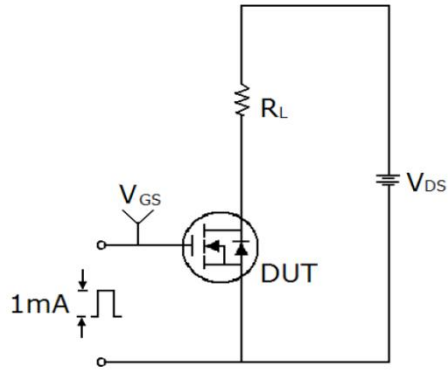

Figure 9. Maximum Safe Operating Area
TO-247

Figure 10. Transient Thermal Impedance
TO-247


Figure 11. Typ. Coss Stored Energy

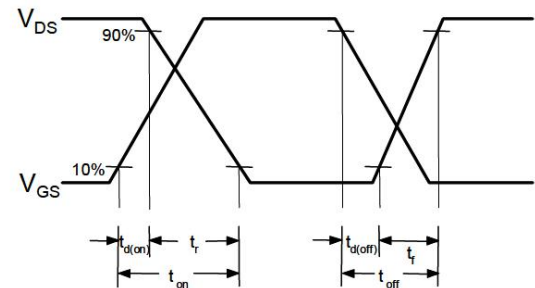
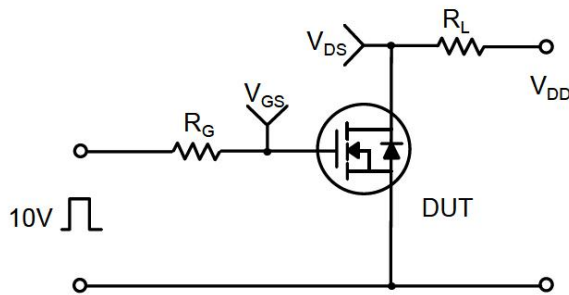


Test Circuits

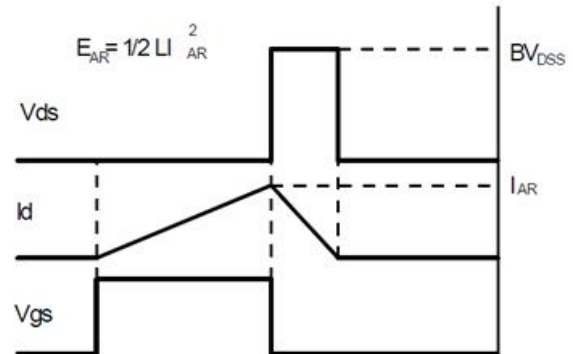
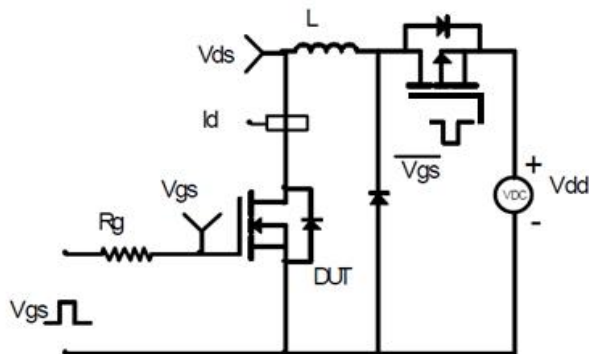
Gate Charge Test Circuit & Waveform



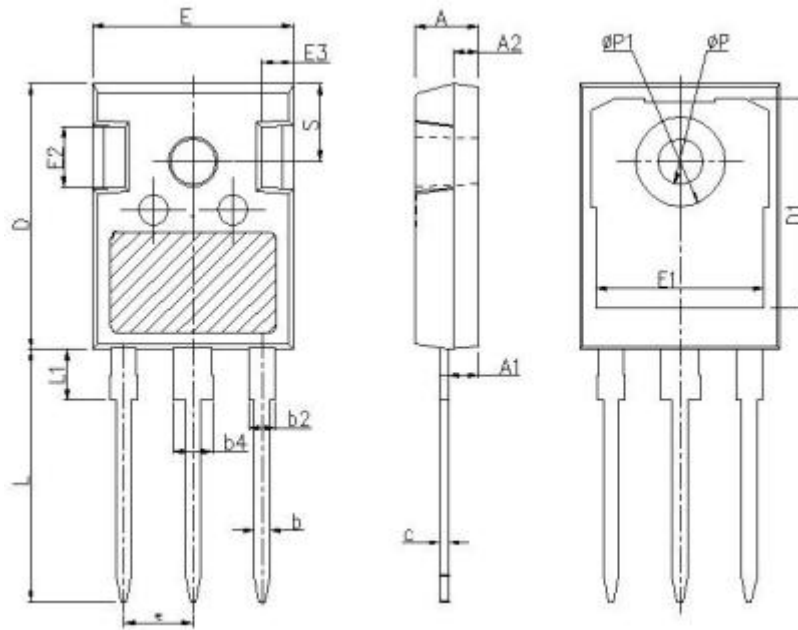
Switching Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveform



Mechanical Dimensions for TO-247



DIMENSIONS IN MILLIMETERS		
SYMBOL	MIN	MAX
A	4.8	5.21
A1	2.21	2.61
A2	1.85	2.16
b	1.07	1.36
b2	1.91	2.41
b4	2.87	3.38
c	0.51	0.75
D	20.7	21.3
D1	16.25	17.65
E	15.5	16.13
E1	13	13.6
E2	3.68	5.2
E3	1	2.7
e	5.44BSC	
L	19.62	20.32
L1	–	4.4
ΦP	3.4	3.8
ΦP1	–	7.4
S	6.04	6.3